



III-V Nitride: Materials, Physics and Devices

Guest Editors:

Dr. Liwen Sang

International Center for Materials
Nanoarchitectonics, National
Institute for Materials Science, 1
Chome Namiki 305-0044, Japan

Dr. Masataka Imura

Senior Researcher, Electric and
Electronic Materials Field, Wide
Bandgap Semiconductors Group,
Research Center for Functional
Materials, National Institute for
Materials Science, 1-1 Namiki,
Tsukuba, Japan

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Message from the Guest Editors

During the last decades, III-V nitrides materials and their optical/electronic devices have been spectacular in many research and applications, such as light emitting diodes (LEDs), laser diodes (LDs), photodiodes, solar cells, RF transistors, and power devices. High-crystalline quality GaN, AlN, AlGaIn, InGaIn layers and their structures have been obtained. Considerable efforts have been made on the material and device physics. Especially, with the recent development of the high-quality free-standing GaN substrate with dislocation density lower than 10^5cm^{-2} , intrinsic material/device physics and high-performance optical/electronic and power devices are highly expected.

The Special Issue of the journal Applied Sciences, 'III-V Nitrides: material, physics and devices', aims to cover the recent advances in the development of III-V nitrides materials and physics properties, as well as the advanced device concepts and developments.





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Editor-in-Chief

Prof. Dr. Giulio Nicola Cerullo

Dipartimento di Fisica,
Politecnico di Milano, Piazza L.
da Vinci 32, 20133 Milano, Italy

Message from the Editor-in-Chief

As the world of science becomes ever more specialized, researchers may lose themselves in the deep forest of the ever increasing number of subfields being created. This open access journal Applied Sciences has been started to link these subfields, so researchers can cut through the forest and see the surrounding, or quite distant fields and subfields to help develop his/her own research even further with the aid of this multi-dimensional network.

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